

Compound Connections

- *Multi-Stage*
- Have some *special properties*
- *Popular Topologies:*
 - *Darlington*
 - *Cascode*
 - *DP* (or *DA*)
- *Modules by themselves*

- ***Darlington:***

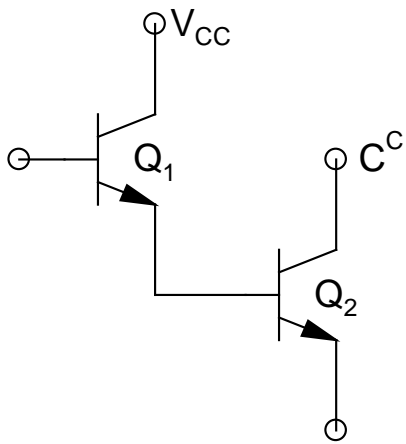
- Cascade of a **CC** stage, followed by either a **CE** or a **CC** stage

- ***Two biggest advantages:***

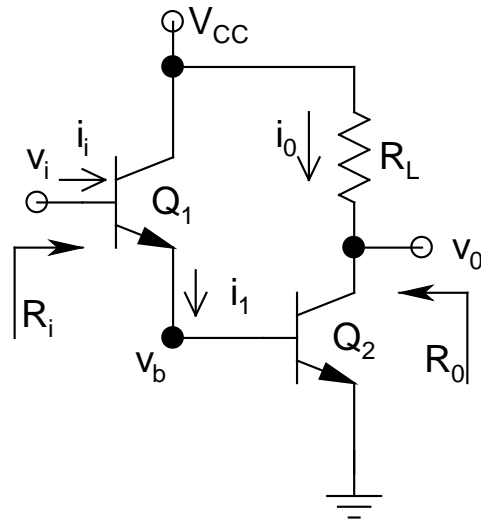
- ***Extremely large R_i***
- ***Extremely large A_i***

- ***These two advantages are automatic for MOS stages***

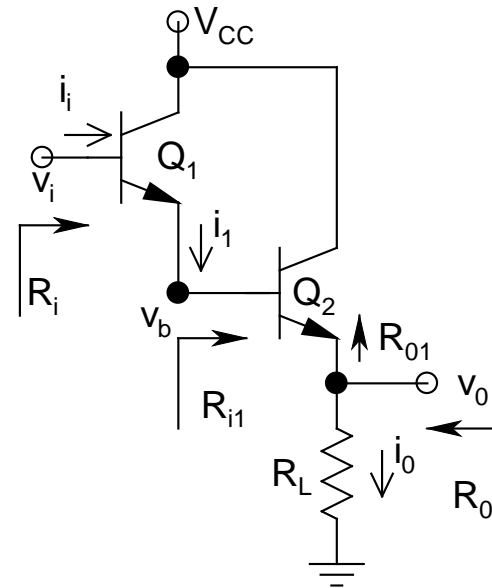
⇒ ***MOS Darlington has no special use***



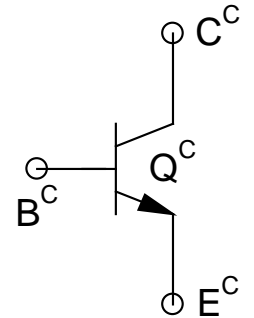
Generic Circuit



CC-CE Stage



CC-CC Stage



Compact Representation

➤ For ***DC biasing***:

$$I_{C2} = \beta_2 I_{B2} = \beta_2 I_{E1} \approx \beta_2 I_{C1}$$

$$\Rightarrow r_{\pi 2} = \beta_2 r_{E2} = \beta_2 V_T / I_{C2} = V_T / I_{C1} = r_{E1}$$

➤ For *ac analysis*:

CC-CE:

- $i_1 = (\beta_1 + 1)i_i$ and $i_0 = \beta_2 i_1 = \beta_2(\beta_1 + 1)i_i$
 $\Rightarrow A_i = i_0/i_i = \beta_2(\beta_1 + 1) \approx \beta^2$ (*Huge!*)
- $R_i = r_{\pi 1} + (\beta_1 + 1)r_{\pi 2} \approx 2r_{\pi 1}$
 - ❖ $I_{C2} \sim \text{mA}$, $I_{C1} \sim 10\text{s of } \mu\text{A}$, $r_{E1} \sim \text{k}\Omega$, $r_{\pi 1} \sim 100\text{s of } \text{k}\Omega$ (*Huge!*)
- $v_0/v_b = -R_L/r_{E2}$ and $v_b/v_i = r_{\pi 2}/(r_{\pi 2} + r_{E1}) = 1/2$
 $\Rightarrow A_v = v_0/v_i = -R_L/(2r_{E2})$ (*Moderate*)
- $R_0 = R_L || r_{02} \approx R_L$ (*Moderate*)

➤ Thus, this stage has *huge A_i and R_i* , and *moderate A_v and R_0*

➤ For *ac analysis*:

CC-CC:

- $i_1 = (\beta_1 + 1)i_i$ and $i_0 = (\beta_2 + 1)i_1 = (\beta_2 + 1)(\beta_1 + 1)i_i$
 $\Rightarrow A_i = i_0/i_i = (\beta_2 + 1)(\beta_1 + 1) \approx \beta^2$ (*Huge!*)
- $R_i = r_{\pi 1} + (\beta_1 + 1)(\beta_2 + 1)(r_{E2} + R_L)$
 $\approx r_{\pi 1} + \beta^2(r_{E2} + R_L)$ (*Astronomical!*)
- $R_{i1} = r_{\pi 2} + (\beta_2 + 1)R_L$
- $v_0/v_b = R_L/(R_L + r_{E2})$
- $v_b/v_i = R_{i1}/(r_{E1} + R_{i1})$
- $A_v = v_0/v_i \approx \beta_2 R_L/(2r_{E1} + \beta_2 R_L)$ (*Show!*)

➤ Thus, this stage has *extremely large A_i and R_i* ,
and *A_v is ≤ 1 with no phase shift*

➤ $R_0 = R_L \parallel R_{01}$

$R_{01} = r_{E2} + r_{E1}/(\beta_2 + 1)$ (*by inspection*)

$\approx 2r_{E2}$

$\Rightarrow R_0 \approx R_L \parallel (2r_{E2})$ (*Small*)

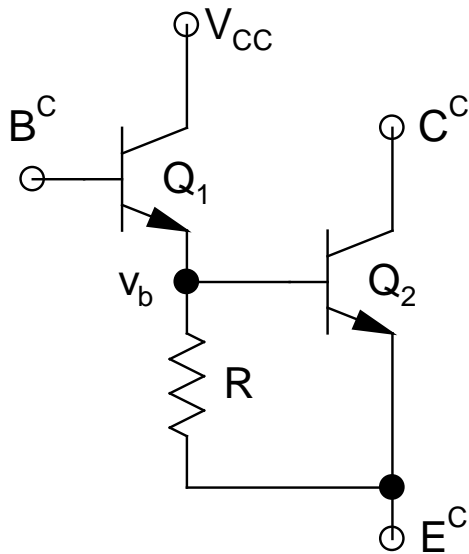
➤ Above analysis is *pretty straightforward*, and *assumes that both β_1 and β_2 are high*

➤ *In reality, Q_1 operates with a very low value of I_C ($\sim 10s$ of μA)*

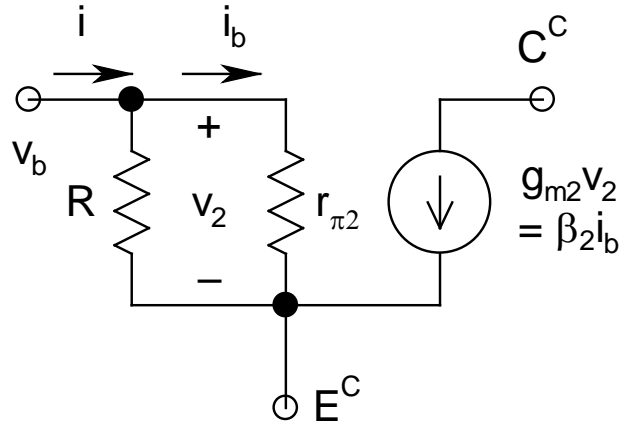
\Rightarrow *β_1 would drop significantly from its nominal value \Rightarrow Full advantage of the circuit can't be exploited*

➤ *Need to jack up β_1*

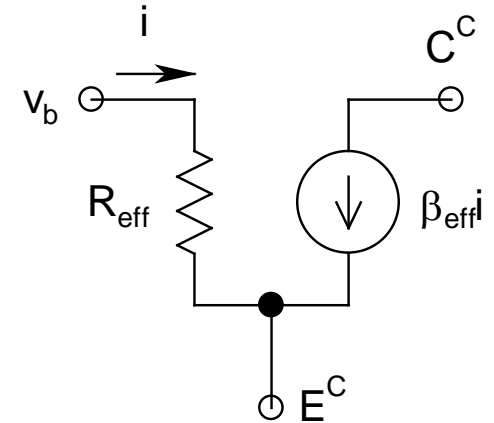
❖ *How about using a keep-alive resistor?*



**Darlington with
Keep-Alive Resistor R**



**ac Midband Equivalent
of Q_2 -R Combination**



**Simplified Equivalent
of Q_2 -R Combination**

- ***R drains a constant DC current of $\sim 0.7/R$***
- ***This current is supplied by Q_1 , along with I_{B2}***
 $\Rightarrow I_{C1} \uparrow \Rightarrow \beta_1 \uparrow$
- ***However, this technique also changes β_2***
- ***Analysis:***

$$i_b = iR/(R + r_{\pi 2})$$

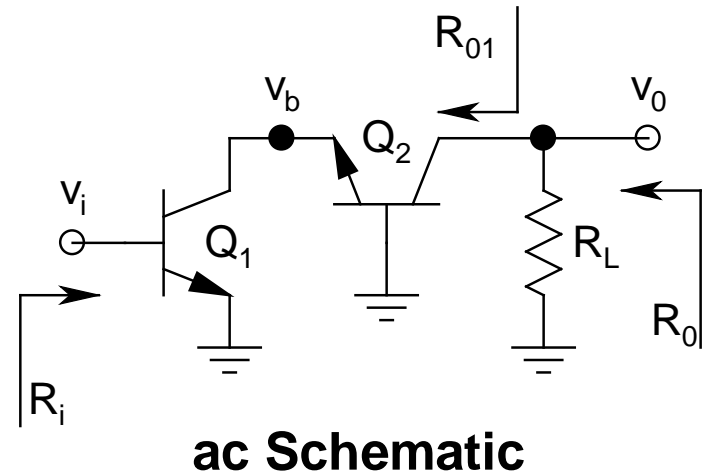
$$\Rightarrow i_c = \beta_2 i_b = \beta_2 iR/(R + r_{\pi 2}) = g_{m2} r_{\pi 2} iR/(R + r_{\pi 2}) = g_{m2} (R || r_{\pi 2}) i = g_{m2} R_{\text{eff}} i = \beta_{\text{eff}} i$$

$$\beta_{\text{eff}} = g_{m2} R_{\text{eff}} < \beta_2 \quad (R_{\text{eff}} = R || r_{\pi 2})$$

- As if $r_{\pi 2, \text{eff}} = R_{\text{eff}}$

- *npn Cascode:*

- *CE*, followed by *CB*
- Known as *Wideband Amplifier*, due to its *superior frequency response characteristic*



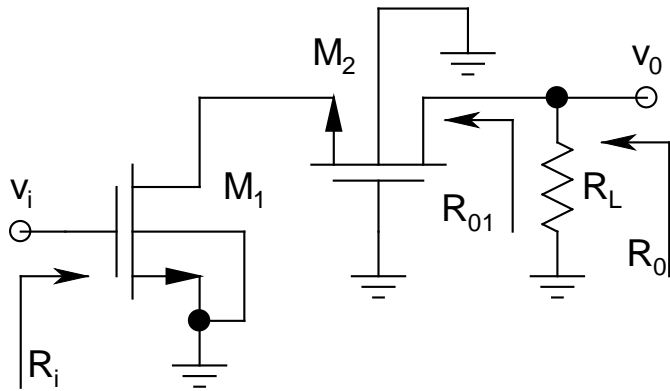
- *Generally, both Q_1 and Q_2 are biased with the same I_C*
- *Assuming Q_1 - Q_2 have same β :*

$$r_{E1} = r_{E2} = r_E \text{ and } r_{\pi1} = r_{\pi2} = r_{\pi}$$

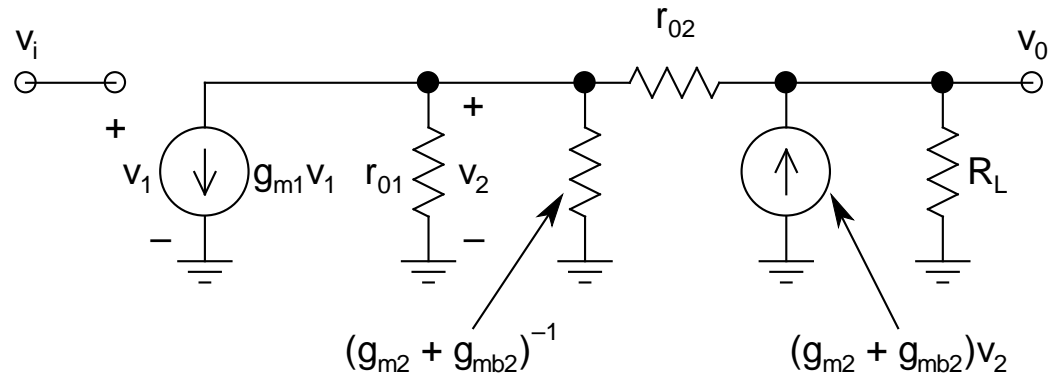
- *This circuit can be analyzed by inspection*
- $R_i = r_{\pi 1}$
- $v_o/v_b = +g_{m2}R_L = R_L/r_{E2}$ (**CB Stage**)
- $v_b/v_i = -r_{E2}/r_{E1} = -1$
 - *CE Stage with R_i of $Q_2 (= r_{E2})$ as its load*
- Thus, $A_v = v_o/v_i = -R_L/r_{E2}$
- *Note that A_v is same as that for a CE stage, however, the bandwidth of this circuit is far superior than a CE stage*

- $R_0 = R_L \parallel R_{01}$
- *If r_o is neglected*, then $R_{01} \rightarrow \infty$ (*why?*)
- *If r_o is included*, then $R_{01} = \beta r_{o2}$ (*very high*)
- However, *it comes in parallel with R_L*
 \Rightarrow *Overall R_0 is still $\sim R_L$*
- *Summary:*
 - *Moderate voltage gain*
 - *Moderate input resistance*
 - *Potential of having very large output resistance*
 - *Extremely large bandwidth*
 - *Preferred over a simple CE stage*

- ***NMOS Cascode:***



ac Schematic



ac Midband Equivalent

- ***CS***, followed by ***CG***
- ***Generally, both M_1 and M_2 are biased with the same I_D***
- ***M_1 does not have body effect, but M_2 has***

- *By inspection*, $R_i \rightarrow \infty$ and $R_0 = R_L || R_{01}$
- *With r_{02} present, the analysis becomes a little complicated \Rightarrow neglect $r_{02} \Rightarrow R_0 = R_L$*
- *Neglecting r_{02} :*

$$v_0 = (g_{m2} + g_{mb2})v_2 R_L$$

$$v_2 = -g_{m1}v_1 / (g_{m2} + g_{mb2} + g_{01}) \quad (g_{01} = 1/r_{01})$$

$$\approx -g_{m1}v_1 / (g_{m2} + g_{mb2})$$

[since, in general, $g_{01} \ll (g_{m2} + g_{mb2})$]

$$\Rightarrow A_v = v_0/v_i = -g_{m1}R_L \quad (\text{since } v_1 = v_i)$$
- *This is same as the CS stage, however, here broad-banding is happening!*

- *A_v gets affected a little if r_{o1} and r_{o2} were included*
- *Since r_{o1} comes in parallel with $(g_{m2} + g_{mb2})^{-1}$, its effect on A_v is less pronounced than that of r_{o2}*
- *By inspection:*

$$R_{o1} \approx (g_{m2} + g_{mb2})r_{o1}r_{o2} \text{ (Show!)}$$
- *Note that if either of r_{o1} or $r_{o2} \rightarrow \infty$, $R_{o1} \rightarrow \infty$ (Why?)*